

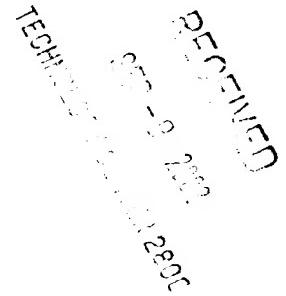
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9/16/02
C. Moore

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :
EIJI SAKAGAMI : EXAMINER: H. WEISS
SERIAL NO.: 09/955,076 :
FILED: SEPTEMBER 19, 2001 : GROUP ART UNIT: 2814
FOR: NONVOLATILE SEMICONDUCTOR MEMORY
AND METHOD OF FABRICATING THE SAME



AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

In response to the Official Action dated June 6, 2002, please amend the above-identified patent application as follows:

IN THE TITLE

Please amend the title as follows:

NONVOLATILE SEMICONDUCTOR MEMORY HAVING MONOS
STRUCTURE AND METHOD OF FABRICATING THE SAME USING
SHALLOW TRENCH ISOLATION

IN THE CLAIMS

Please amend Claim 1 to read as follows:¹

1. (Amended) A nonvolatile semiconductor memory comprising:
a semiconductor substrate;

¹The changes to Claim 1 are denoted using underscoring and bracketing in the marked-up copy herewith.